

# Manijeh Razeghi

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

323 papers	12,755 citations	61 h-index	94 g-index
355 ext. papers	14,297 ext. citations	3.5 avg, IF	6.48 L-index

#	Paper	IF	Citations
323	High Power Mid-Infrared Quantum Cascade Lasers Grown on GaAs. <i>Photonics</i> , <b>2022</b> , 9, 231	2.2	2
322	Low Dark Current Deep UV AlGaIn Photodetectors on AlN Substrate. <i>IEEE Journal of Quantum Electronics</i> , <b>2022</b> , 58, 1-5	2	0
321	Highly Conductive Co-Doped Ga <sub>2</sub> O <sub>3</sub> :Si-In Grown by MOCVD. <i>Coatings</i> , <b>2021</b> , 11, 287	2.9	4
320	Performance analysis of infrared heterojunction phototransistors based on Type-II superlattices. <i>Infrared Physics and Technology</i> , <b>2021</b> , 113, 103641	2.7	2
319	Mid-wavelength infrared avalanche photodetector with AlAsSb/GaSb superlattice. <i>Scientific Reports</i> , <b>2021</b> , 11, 7104	4.9	5
318	Low Noise Short Wavelength Infrared Avalanche Photodetector Using SB-Based Strained Layer Superlattice. <i>Photonics</i> , <b>2021</b> , 8, 148	2.2	1
317	Geiger-Mode Operation of AlGaIn Avalanche Photodiodes at 255 nm. <i>IEEE Journal of Quantum Electronics</i> , <b>2021</b> , 57, 1-6	2	4
316	Harmonic injection locking of high-power mid-infrared quantum cascade lasers. <i>Photonics Research</i> , <b>2021</b> , 9, 1078	6	1
315	Resonant cavity enhanced heterojunction phototransistors based on type-II superlattices. <i>Infrared Physics and Technology</i> , <b>2021</b> , 113, 103552	2.7	3
314	Multi-band SWIR-MWIR-LWIR Type-II superlattice based infrared photodetector. <i>Results in Optics</i> , <b>2021</b> , 2, 100054	1	5
313	Study of Phase Transition in MOCVD Grown Ga <sub>2</sub> O <sub>3</sub> from $\Gamma$ to $\Gamma$ Phase by Ex Situ and In Situ Annealing. <i>Photonics</i> , <b>2021</b> , 8, 17	2.2	7
312	High Power, Widely Tunable, and Beam Steerable Mid-infrared Quantum Cascade Lasers. <i>NATO Science for Peace and Security Series B: Physics and Biophysics</i> , <b>2021</b> , 21-34	0.2	
311	High-brightness LWIR quantum cascade lasers. <i>Optics Letters</i> , <b>2021</b> , 46, 5193-5196	3	2
310	Band-structure-engineered high-gain LWIR photodetector based on a type-II superlattice. <i>Light: Science and Applications</i> , <b>2021</b> , 10, 17	16.7	9
309	Microstrip Array Ring FETs with 2D p-Ga <sub>2</sub> O <sub>3</sub> Channels Grown by MOCVD. <i>Photonics</i> , <b>2021</b> , 8, 578	2.2	0
308	Avalanche Photodetector Based on InAs/InSb Superlattice. <i>Quantum Reports</i> , <b>2020</b> , 2, 591-599	2.1	6
307	Type-II superlattice-based heterojunction phototransistors for high speed applications. <i>Infrared Physics and Technology</i> , <b>2020</b> , 108, 103350	2.7	7

306	Planar nBn type-II superlattice mid-wavelength infrared photodetectors using zinc ion-implantation. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 221103	3.4	8
305	Mid-wavelength infrared high operating temperature pBn photodetectors based on type-II InAs/InAsSb superlattice. <i>AIP Advances</i> , <b>2020</b> , 10, 025018	1.5	23
304	High power continuous wave operation of single mode quantum cascade lasers up to 5 W spanning 3.8-8.3 $\mu\text{m}$ . <i>Optics Express</i> , <b>2020</b> , 28, 15181-15188	3.3	2
303	Room temperature quantum cascade lasers with 22% wall plug efficiency in continuous-wave operation. <i>Optics Express</i> , <b>2020</b> , 28, 17532-17538	3.3	9
302	Continuous wave quantum cascade lasers with 5.6 W output power at room temperature and 41% wall-plug efficiency in cryogenic operation. <i>AIP Advances</i> , <b>2020</b> , 10, 055120	1.5	4
301	InAs/GaSb type II superlattices: A developing material system for third generation of IR imaging <b>2020</b> , 379-413		5
300	Demonstration of Planar Type-II Superlattice-Based Photodetectors Using Silicon Ion-Implantation. <i>Photonics</i> , <b>2020</b> , 7, 68	2.2	2
299	Room temperature quantum cascade laser with ~31% wall-plug efficiency. <i>AIP Advances</i> , <b>2020</b> , 10, 075012	1.5	6
298	High performance InAs/InAsSb Type-II superlattice mid-wavelength infrared photodetectors with double barrier. <i>Infrared Physics and Technology</i> , <b>2020</b> , 109, 103439	2.7	7
297	High performance Zn-diffused planar mid-wavelength infrared type-II InAs/InAs <sub>1-x</sub> Sb <sub>x</sub> superlattice photodetector by MOCVD. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 161108	3.4	8
296	Surface Emitting, Tunable, Mid-Infrared Laser with High Output Power and Stable Output Beam. <i>Scientific Reports</i> , <b>2019</b> , 9, 549	4.9	5
295	Extended short wavelength infrared heterojunction phototransistors based on type II superlattices. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 191109	3.4	12
294	Ga <sub>2</sub> O <sub>3</sub> metal-oxide-semiconductor field effect transistors on sapphire substrate by MOCVD. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 08LT01	1.8	12
293	Room temperature terahertz semiconductor frequency comb. <i>Nature Communications</i> , <b>2019</b> , 10, 2403	17.4	28
292	AlGa <sub>N</sub> /Al <sub>N</sub> MOVPE heteroepitaxy: pulsed co-doping SiH <sub>4</sub> and TMIn. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 075028	1.8	5
291	Investigation of surface leakage reduction for small pitch shortwave infrared photodetectors. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 06LT01	1.8	2
290	Type-II superlattices base visible/extended short-wavelength infrared photodetectors with a bandstructure-engineered photo-generated carrier extractor. <i>Scientific Reports</i> , <b>2019</b> , 9, 5003	4.9	16
289	Demonstration of mid-wavelength infrared nBn photodetectors based on type-II InAs/InAs <sub>1-x</sub> Sb <sub>x</sub> superlattice grown by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 061102	3.4	10

288	MOCVD grown $\text{InGa2O3}$ metal-oxide-semiconductor field effect transistors on sapphire. <i>Applied Physics Express</i> , <b>2019</b> , 12, 095503	2.4	9
287	High speed antimony-based superlattice photodetectors transferred on sapphire. <i>Applied Physics Express</i> , <b>2019</b> , 12, 116502	2.4	5
286	Antimonite-based gap-engineered type-II superlattice materials grown by MBE and MOCVD for the third generation of infrared imagers <b>2019</b> ,		4
285	High-power, continuous-wave, phase-locked quantum cascade laser arrays emitting at 8 $\mu\text{m}$ . <i>Optics Express</i> , <b>2019</b> , 27, 15776-15785	3.3	16
284	Fabrication of 12 $\mu\text{m}$ pixel-pitch 1280 $\times$ 1024 extended short wavelength infrared focal plane array using heterojunction type-II superlattice-based photodetectors. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 03LT01	1.8	7
283	Suppressing Spectral Crosstalk in Dual-Band Long- Wavelength Infrared Photodetectors With Monolithically Integrated Air-Gapped Distributed Bragg Reflectors. <i>IEEE Journal of Quantum Electronics</i> , <b>2019</b> , 55, 1-6	2	8
282	High quantum efficiency mid-wavelength infrared type-II InAs/InAs <sub>1-x</sub> Sb <sub>x</sub> superlattice photodiodes grown by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 011104	3.4	17
281	Strain-Induced Metastable Phase Stabilization in GaO Thin Films. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 5536-5543	9.5	25
280	High brightness ultraviolet light-emitting diodes grown on patterned silicon substrate. <i>Materials Science in Semiconductor Processing</i> , <b>2019</b> , 90, 87-91	4.3	9
279	Thin-Film Antimonide-Based Photodetectors Integrated on Si. <i>IEEE Journal of Quantum Electronics</i> , <b>2018</b> , 54, 1-7	2	8
278	Shortwave quantum cascade laser frequency comb for multi-heterodyne spectroscopy. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 141104	3.4	20
277	Sandwich method to grow high quality AlN by MOCVD. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 085104	1.4	19
276	Phase-locked, high power, mid-infrared quantum cascade laser arrays. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 181106	3.4	10
275	Room temperature operation of In <sub>x</sub> Ga <sub>1-x</sub> Sb/InAs type-II quantum well infrared photodetectors grown by MOCVD. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 111103	3.4	18
274	nBn extended short-wavelength infrared focal plane array. <i>Optics Letters</i> , <b>2018</b> , 43, 591-594	3	26
273	Type-II InAs/GaSb/AlSb superlattice-based heterojunction phototransistors: back to the future <b>2018</b> ,		2
272	Single-mode, high-power, mid-infrared, quantum cascade laser phased arrays. <i>Scientific Reports</i> , <b>2018</b> , 8, 14866	4.9	11
271	. <i>IEEE Journal of Quantum Electronics</i> , <b>2018</b> , 54, 1-5	2	5

270	Demonstration of long wavelength infrared type-II InAs/InAs <sub>1-x</sub> Sb <sub>x</sub> superlattices photodiodes on GaSb substrate grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 241103	3.4	14
269	Impact of scaling base thickness on the performance of heterojunction phototransistors. <i>Nanotechnology</i> , <b>2017</b> , 28, 10LT01	3.4	17
268	A lifetime of contributions to the world of semiconductors using the Czochralski invention. <i>Vacuum</i> , <b>2017</b> , 146, 308-328	3.7	1
267	Background-limited long wavelength infrared InAs/InAs <sub>1-x</sub> Sb <sub>x</sub> type-II superlattice-based photodetectors operating at 110 K. <i>APL Materials</i> , <b>2017</b> , 5, 035502	5.7	28
266	High efficiency quantum cascade laser frequency comb. <i>Scientific Reports</i> , <b>2017</b> , 7, 43806	4.9	16
265	Extended short-wavelength infrared nBn photodetectors based on type-II InAs/AlSb/GaSb superlattices with an AlAsSb/GaSb superlattice barrier. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 101104	3.4	38
264	Recent advances in InAs/InAs <sub>1-x</sub> Sb <sub>x</sub> /AlAs <sub>1-x</sub> Sb <sub>x</sub> gap-engineered type-II superlattice-based photodetectors <b>2017</b> ,		10
263	Dispersion compensated mid-infrared quantum cascade laser frequency comb with high power output. <i>AIP Advances</i> , <b>2017</b> , 7, 045313	1.5	8
262	Bias-selectable nBn dual-band long-/very long-wavelength infrared photodetectors based on InAs/InAsSb/AlAsSb type-II superlattices. <i>Scientific Reports</i> , <b>2017</b> , 7, 3379	4.9	39
261	Preface to Special Topic: Emerging materials for photonics. <i>APL Materials</i> , <b>2017</b> , 5, 035101	5.7	
260	Study of Au coated ZnO nanoarrays for surface enhanced Raman scattering chemical sensing. <i>Journal of Materials Chemistry C</i> , <b>2017</b> , 5, 3528-3535	7.1	38
259	Dark current reduction in microjunction-based double electron barrier type-II InAs/InAsSb superlattice long-wavelength infrared photodetectors. <i>Scientific Reports</i> , <b>2017</b> , 7, 12617	4.9	11
258	Monolithic beam steering in a mid-infrared, surface-emitting, photonic integrated circuit. <i>Scientific Reports</i> , <b>2017</b> , 7, 8472	4.9	5
257	Direct growth of thick AlN layers on nanopatterned Si substrates by cantilever epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1600363	1.6	12
256	Bias-selectable three-color short-, extended-short-, and mid-wavelength infrared photodetectors based on type-II InAs/GaSb/AlSb superlattices. <i>Optics Letters</i> , <b>2017</b> , 42, 4275-4278	3	11
255	High performance monolithic, broadly tunable mid-infrared quantum cascade lasers. <i>Optica</i> , <b>2017</b> , 4, 1228	8.6	20
254	Type-II superlattice-based extended short-wavelength infrared focal plane array with an AlAsSb/GaSb superlattice etch-stop layer to allow near-visible light detection. <i>Optics Letters</i> , <b>2017</b> , 42, 4299-4302	3	17
253	Recent progress of quantum cascade laser research from 3 to 12 $\mu$ m at the Center for Quantum Devices [Invited]. <i>Applied Optics</i> , <b>2017</b> , 56, H30-H44	1.7	40

252	Progress in monolithic, broadband, widely tunable midinfrared quantum cascade lasers. <i>Optical Engineering</i> , <b>2017</b> , 57, 1	1.1	3
251	Monolithically, widely tunable quantum cascade lasers based on a heterogeneous active region design. <i>Scientific Reports</i> , <b>2016</b> , 6, 25213	4.9	30
250	High performance bias-selectable three-color Short-wave/Mid-wave/Long-wave Infrared Photodetectors based on Type-II InAs/GaSb/AlSb superlattices. <i>Scientific Reports</i> , <b>2016</b> , 6, 24144	4.9	63
249	Room temperature continuous wave, monolithic tunable THz sources based on highly efficient mid-infrared quantum cascade lasers. <i>Scientific Reports</i> , <b>2016</b> , 6, 23595	4.9	57
248	Mid-wavelength infrared heterojunction phototransistors based on type-II InAs/AlSb/GaSb superlattices. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 021107	3.4	23
247	High brightness angled cavity quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 091105	3.4	42
246	Quantum cascade lasers: from tool to product. <i>Optics Express</i> , <b>2015</b> , 23, 8462-75	3.3	117
245	Ultra-broadband quantum cascade laser, tunable over 760 cm <sup>-1</sup> , with balanced gain. <i>Optics Express</i> , <b>2015</b> , 23, 21159-64	3.3	29
244	High power continuous operation of a widely tunable quantum cascade laser with an integrated amplifier. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 251101	3.4	16
243	High-performance short-wavelength infrared photodetectors based on type-II InAs/InAs <sub>1-x</sub> Sbx/AlAs <sub>1-x</sub> Sbx superlattices. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 141104	3.4	34
242	High power frequency comb based on mid-infrared quantum cascade laser at 9 $\mu$ m. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 051105	3.4	39
241	Quantum Dots <b>2015</b> , 169-219		1
240	Bias-selectable dual-band mid-/long-wavelength infrared photodetectors based on InAs/InAs <sub>1-x</sub> Sbx type-II superlattices. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 011104	3.4	62
239	Generation-recombination and trap-assisted tunneling in long wavelength infrared minority electron unipolar photodetectors based on InAs/GaSb superlattice. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 053508	3.4	21
238	Continuous operation of a monolithic semiconductor terahertz source at room temperature. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 221105	3.4	62
237	Advances in mid-infrared detection and imaging: a key issues review. <i>Reports on Progress in Physics</i> , <b>2014</b> , 77, 082401	14.4	80
236	InAs/InAs <sub>1-x</sub> Sbx type-II superlattices for high performance long wavelength infrared detection. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 121104	3.4	85
235	High Performance Solar-Blind Ultraviolet (320 times 256) Focal Plane Arrays Based on Al <sub>x</sub> Ga <sub>1-x</sub> N. <i>IEEE Journal of Quantum Electronics</i> , <b>2014</b> , 50, 593-597	2	7

234	Measurements of carbon monoxide mixing ratios in Houston using a compact high-power CW DFB-QCL-based QEPAS sensor. <i>Applied Physics B: Lasers and Optics</i> , <b>2014</b> , 117, 519-526	1.9	7
233	Antimonide-Based Type II Superlattices: A Superior Candidate for the Third Generation of Infrared Imaging Systems. <i>Journal of Electronic Materials</i> , <b>2014</b> , 43, 2802-2807	1.9	22
232	High performance photodiodes based on InAs/InAsSb type-II superlattices for very long wavelength infrared detection. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 251105	3.4	58
231	Superlattice-based quantum devices: from theory to practical applications. <i>Waves in Random and Complex Media</i> , <b>2014</b> , 24, 240-249	1.9	
230	Widely tunable room temperature semiconductor terahertz source. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 201102	3.4	53
229	Investigation of impurities in type-II InAs/GaSb superlattices via capacitance-voltage measurement. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 033512	3.4	12
228	Surface plasmon enhanced light emission from AlGaIn-based ultraviolet light-emitting diodes grown on Si (111). <i>Applied Physics Letters</i> , <b>2013</b> , 102, 211110	3.4	65
227	Demonstration of high performance bias-selectable dual-band short-/mid-wavelength infrared photodetectors based on type-II InAs/GaSb/AlSb superlattices. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 011108	3.4	39
226	Al <sub>x</sub> Ga <sub>1-x</sub> N-based back-illuminated solar-blind photodetectors with external quantum efficiency of 89%. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 191108	3.4	107
225	Near milliwatt power AlGaIn-based ultraviolet light emitting diodes based on lateral epitaxial overgrowth of AlN on Si(111). <i>Applied Physics Letters</i> , <b>2013</b> , 102, 011106	3.4	41
224	Type II Antimonide-Based Superlattices: A One-Dimensional Bulk Semiconductor <b>2013</b> , 415-434		
223	Advances in antimonide-based Type-II superlattices for infrared detection and imaging at center for quantum devices. <i>Infrared Physics and Technology</i> , <b>2013</b> , 59, 41-52	2.7	52
222	Crack-free AlGaIn for solar-blind focal plane arrays through reduced area epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 051102	3.4	28
221	Room temperature terahertz quantum cascade laser sources with 215 W output power through epilayer-down mounting. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 011101	3.4	38
220	Al <sub>x</sub> Ga <sub>1-x</sub> N-based solar-blind ultraviolet photodetector based on lateral epitaxial overgrowth of AlN on Si substrate. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 181113	3.4	31
219	Active and passive infrared imager based on short-wave and mid-wave type-II superlattice dual-band detectors. <i>Optics Letters</i> , <b>2013</b> , 38, 22-4	3	21
218	Extended electrical tuning of quantum cascade lasers with digital concatenated gratings. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 231110	3.4	33
217	High performance terahertz quantum cascade laser sources based on intracavity difference frequency generation. <i>Optics Express</i> , <b>2013</b> , 21, 968-73	3.3	31



216	High Operability 1024 $\times$ 1024 Long Wavelength Type-II Superlattice Focal Plane Array. <i>IEEE Journal of Quantum Electronics</i> , <b>2012</b> , 48, 221-228	2	26
215	Surface leakage investigation via gated type-II InAs/GaSb long-wavelength infrared photodetectors. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 213501	3-4	19
214	High power, continuous wave, room temperature operation of $\sim$ 3.4 $\mu$ m and $\sim$ 3.55 $\mu$ m InP-based quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 212104	3-4	58
213	Highly selective two-color mid-wave and long-wave infrared detector hybrid based on Type-II superlattices. <i>Optics Letters</i> , <b>2012</b> , 37, 4744-6	3	29
212	Sampled grating, distributed feedback quantum cascade lasers with broad tunability and continuous operation at room temperature. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 261112	3-4	55
211	Demonstration of shortwavelength infrared photodiodes based on type-II InAs/GaSb/AlSb superlattices. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 211101	3-4	80
210	Room temperature continuous wave operation of $\sim$ 3.2 $\mu$ m quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 241110	3-4	82
209	Thermal Conductivity of InAs/GaSb Type II Superlattice. <i>Journal of Electronic Materials</i> , <b>2012</b> , 41, 2322-2325		8
208	World's first demonstration of type-II superlattice dual band 640x512 LWIR focal plane array <b>2012</b> ,		9
207	Al(x)Ga(1-x)N-based deep-ultraviolet 320 $\times$ 56 focal plane array. <i>Optics Letters</i> , <b>2012</b> , 37, 896-8	3	29
206	Widely tuned room temperature terahertz quantum cascade laser sources based on difference-frequency generation. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 251121	3-4	43
205	High Operability 1024 $\times$ 1024 Long Wavelength Infrared Focal Plane Array Base on Type-II InAs/GaSb Superlattice <b>2011</b> ,		3
204	Room temperature single-mode terahertz sources based on intracavity difference-frequency generation in quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 131106	3-4	61
203	Room temperature quantum cascade lasers with 27% wall plug efficiency. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 181102	3-4	228
202	2.4 W room temperature continuous wave operation of distributed feedback quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 181106	3-4	88
201	High operating temperature midwave infrared photodiodes and focal plane arrays based on type-II InAs/GaSb superlattices. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 143501	3-4	89
200	Type-II superlattice dual-band LWIR imager with M-barrier and Fabry-Perot resonance. <i>Optics Letters</i> , <b>2011</b> , 36, 2560-2	3	32
199	Growth and Characterization of Long-Wavelength Infrared Type-II Superlattice Photodiodes on a 3-in GaSb Wafer. <i>IEEE Journal of Quantum Electronics</i> , <b>2011</b> , 47, 686-690	2	52



198	Type-II InAs/GaSb photodiodes and focal plane arrays aimed at high operating temperatures. <i>Opto-electronics Review</i> , <b>2011</b> , 19,	2.4	29
197	Surface leakage current reduction in long wavelength infrared type-II InAs/GaSb superlattice photodiodes. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 183501	3.4	23
196	Elimination of surface leakage in gate controlled type-II InAs/GaSb mid-infrared photodetectors. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 183503	3.4	29
195	High power, continuous wave, quantum cascade ring laser. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 261104	3.4	37
194	Deep ultraviolet (254 nm) focal plane array <b>2011</b> ,		4
193	Widely tunable single-mode high power quantum cascade lasers <b>2011</b> ,		6
192	Quantum cascade lasers that emit more light than heat. <i>Nature Photonics</i> , <b>2010</b> , 4, 99-102	33.9	104
191	Highly temperature insensitive quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 251104	3.4	59
190	On the interface properties of ZnO/Si electroluminescent diodes. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 033719	2.5	12
189	GaN avalanche photodiodes grown on m-plane freestanding GaN substrate. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 201908	3.4	31
188	Watt level performance of quantum cascade lasers in room temperature continuous wave operation at $\lambda$ 3.76 $\mu$ m. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 131117	3.4	53
187	Demonstration of negative differential resistance in GaN/AlN resonant tunneling diodes at room temperature. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 083505	2.5	33
186	Room temperature negative differential resistance characteristics of polar III-nitride resonant tunneling diodes. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 092104	3.4	38
185	AlN/GaN double-barrier resonant tunneling diodes grown by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 042103	3.4	76
184	Broad area photonic crystal distributed feedback quantum cascade lasers emitting 34 W at $\lambda$ 4.36 $\mu$ m. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 131112	3.4	40
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43	Second harmonic generation in hexagonal silicon carbide. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 1883-1885	3-4	32
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32	Photoconductance measurements on InTlSb/InSb/GaAs grown by low-pressure metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 460-462	3-4	34
31	Intersubband hole absorption in GaAs-GaInP quantum wells grown by gas source molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 1130-1132	3-4	6
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1	The MOCVD Challenge		21

